

# 深圳市晶泰源电子有限公司

## MMBTA92 TRANSISTOR (PNP)

### FEATURES

High voltage transistor

MARKING:2D

MAXIMUM RATINGS ( $T_A=25^{\circ}\text{C}$  unless otherwise noted)



Symbol	Parameter	Value	Units
$V_{CBO}$	Collector-Base Voltage	-300	V
$V_{CEO}$	Collector-Emitter Voltage	-300	V
$V_{EBO}$	Emitter-Base Voltage	-5	V
$I_C$	Collector Current -Continuous	-300	mA
$P_C$	Collector Power Dissipation	300	mW
$T_j$	Junction Temperature	150	$^{\circ}\text{C}$
$T_{stg}$	Storage Temperature	-55-150	$^{\circ}\text{C}$
$R_{\theta JA}$	Thermal Resistance, junction to Ambient	410	$^{\circ}\text{C}/\text{mW}$

ELECTRICAL CHARACTERISTICS ( $T_{amb}=25^{\circ}\text{C}$  unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu\text{A}, I_E = 0$	-300		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1\text{mA}, I_B = 0$	-300		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100\mu\text{A}, I_C = 0$	-5		V
Collector cut-off current	$I_{CBO}$	$V_{CB} = -200\text{V}, I_E = 0$		-0.25	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB} = -5\text{V}, I_C = 0$		-0.1	$\mu\text{A}$
DC current gain	$h_{FE(1)}$	$V_{CE} = -10\text{V}, I_C = -1\text{mA}$	60		
	$h_{FE(2)}$	$V_{CE} = -10\text{V}, I_C = -10\text{mA}$	100	200	
	$h_{FE(3)}$	$V_{CE} = -10\text{V}, I_C = -30\text{mA}$	60		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -20\text{mA}, I_B = -2\text{mA}$		-0.2	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -20\text{mA}, I_B = -2\text{mA}$		-0.9	V
Transition frequency	$f_T$	$V_{CE} = -20\text{V}, I_C = -10\text{mA}$ $f = 30\text{MHz}$	50		MHz